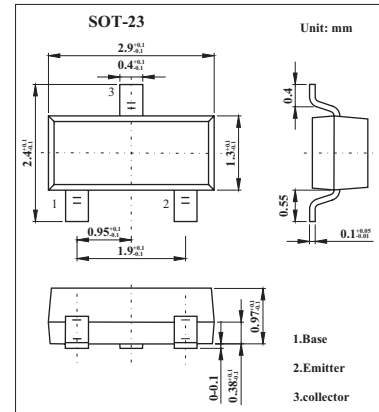


PNP Epitaxial Planar Silicon Transistors

2SA1179

■ Features

- High breakdown voltage

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CB0}	-55	V
Collector-emitter voltage	V_{CE0}	-50	V
Emitter-base voltage	V_{EB0}	-5	V
Collector current	I_C	-150	mA
Collector dissipation	P_C	200	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-50 to 150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CB0}	$I_C = -10\mu\text{A}$, $I_E = 0\text{A}$	-55			V
Collector-emitter breakdown voltage	V_{CE0}	$I_C = -1\text{mA}$, $R_{BE} = \infty$	-50			V
Emitter-base breakdown voltage	V_{EB0}	$I_E = -10\mu\text{A}$, $I_C = 0\text{A}$	-5			V
Collector cutoff current	I_{CBO}	$V_{CB} = -35\text{V}$, $I_E = 0\text{A}$			-0.1	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = -4\text{V}$, $I_C = 0$			-0.1	μA
DC current Gain	h_{FE}	$V_{CE} = -6\text{V}$, $I_C = -1\text{mA}$	200		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -50\text{mA}$, $I_B = -5\text{mA}$			-0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -50\text{mA}$, $I_B = -5\text{mA}$			-1.0	V
Output capacitance	C_{ob}	$V_{CB} = -6\text{V}$, $I_E = 0$, $f = 1\text{MHz}$		4.0		pF
Transition frequency	f_T	$V_{CE} = -6\text{V}$, $I_C = -10\text{mA}$		180		MHz

■ Marking

Marking	M
---------	---